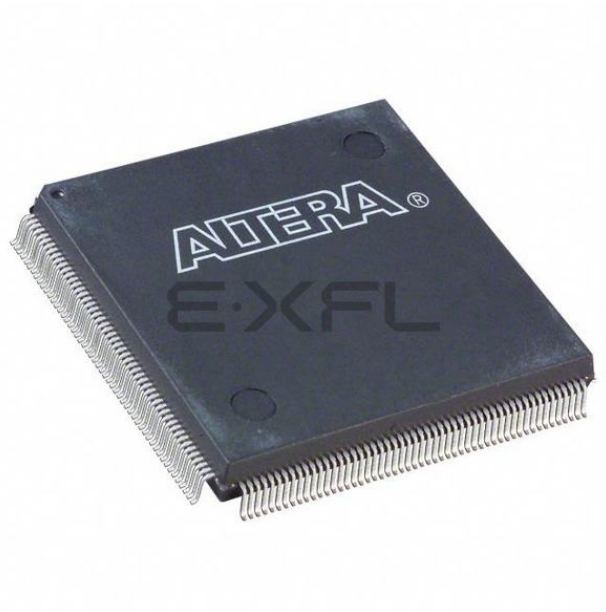
Intel - EP20K60EQC208-3 Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	2560
Number of Logic Elements/Cells	2560
Total RAM Bits	32768
Number of I/O	148
Number of Gates	162000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k60eqc208-3

Table 5. APEX 20K FineLine BGA Package Options & I/O Count *Notes (1), (2)*

Device	144 Pin	324 Pin	484 Pin	672 Pin	1,020 Pin
EP20K30E	93	128			
EP20K60E	93	196			
EP20K100		252			
EP20K100E	93	246			
EP20K160E			316		
EP20K200			382		
EP20K200E			376	376	
EP20K300E				408	
EP20K400				502 *(3)*	
EP20K400E				488 *(3)*	
EP20K600E				508 *(3)*	588
EP20K1000E				508 *(3)*	708
EP20K1500E					808

Notes to Tables 4 and 5:

(1) I/O counts include dedicated input and clock pins.

(2) APEX 20K device package types include thin quad flat pack (TQFP), plastic quad flat pack (PQFP), power quad flat pack (RQFP), 1.27-mm pitch ball-grid array (BGA), 1.00-mm pitch FineLine BGA, and pin-grid array (PGA) packages.

(3) This device uses a thermally enhanced package, which is taller than the regular package. Consult the *Altera Device Package Information Data Sheet* for detailed package size information.

Table 6. APEX 20K QFP, BGA & PGA Package Sizes

Feature	144-Pin TQFP	208-Pin QFP	240-Pin QFP	356-Pin BGA	652-Pin BGA	655-Pin PGA
Pitch (mm)	0.50	0.50	0.50	1.27	1.27	–
Area (mm^2)	484	924	1,218	1,225	2,025	3,906
Length × Width (mm × mm)	22 × 22	30.4 × 30.4	34.9 × 34.9	35 × 35	45 × 45	62.5 × 62.5

Table 7. APEX 20K FineLine BGA Package Sizes

Feature	144 Pin	324 Pin	484 Pin	672 Pin	1,020 Pin
Pitch (mm)	1.00	1.00	1.00	1.00	1.00
Area (mm^2)	169	361	529	729	1,089
Length × Width (mm × mm)	13 × 13	19 × 19	23 × 23	27 × 27	33 × 33

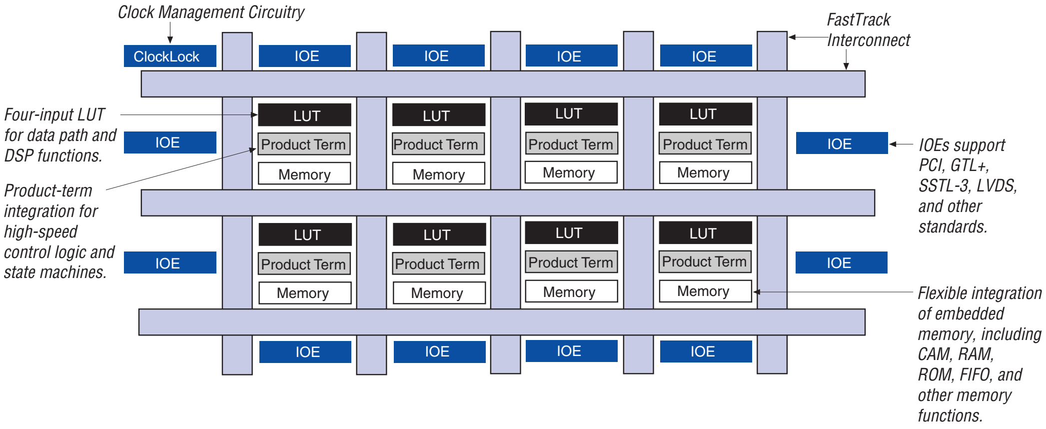
Functional Description

APEX 20K devices incorporate LUT-based logic, product-term-based logic, and memory into one device. Signal interconnections within APEX 20K devices (as well as to and from device pins) are provided by the FastTrack® Interconnect—a series of fast, continuous row and column channels that run the entire length and width of the device.

Each I/O pin is fed by an I/O element (IOE) located at the end of each row and column of the FastTrack Interconnect. Each IOE contains a bidirectional I/O buffer and a register that can be used as either an input or output register to feed input, output, or bidirectional signals. When used with a dedicated clock pin, these registers provide exceptional performance. IOEs provide a variety of features, such as 3.3-V, 64-bit, 66-MHz PCI compliance; JTAG BST support; slew-rate control; and tri-state buffers. APEX 20KE devices offer enhanced I/O support, including support for 1.8-V I/O, 2.5-V I/O, LVCMOS, LVTTL, LVPECL, 3.3-V PCI, PCI-X, LVDS, GTL+, SSTL-2, SSTL-3, HSTL, CTT, and 3.3-V AGP I/O standards.

The ESB can implement a variety of memory functions, including CAM, RAM, dual-port RAM, ROM, and FIFO functions. Embedding the memory directly into the die improves performance and reduces die area compared to distributed-RAM implementations. Moreover, the abundance of cascadable ESBs ensures that the APEX 20K device can implement multiple wide memory blocks for high-density designs. The ESB's high speed ensures it can implement small memory blocks without any speed penalty. The abundance of ESBs ensures that designers can create as many different-sized memory blocks as the system requires. Figure 1 shows an overview of the APEX 20K device.

Figure 1. APEX 20K Device Block Diagram



APEX 20K devices provide two dedicated clock pins and four dedicated input pins that drive register control inputs. These signals ensure efficient distribution of high-speed, low-skew control signals. These signals use dedicated routing channels to provide short delays and low skews. Four of the dedicated inputs drive four global signals. These four global signals can also be driven by internal logic, providing an ideal solution for a clock divider or internally generated asynchronous clear signals with high fan-out. The dedicated clock pins featured on the APEX 20K devices can also feed logic. The devices also feature ClockLock and ClockBoost clock management circuitry. APEX 20KE devices provide two additional dedicated clock pins, for a total of four dedicated clock pins.

MegaLAB Structure

APEX 20K devices are constructed from a series of MegaLAB™ structures. Each MegaLAB structure contains a group of logic array blocks (LABs), one ESB, and a MegaLAB interconnect, which routes signals within the MegaLAB structure. The EP20K30E device has 10 LABs, EP20K60E through EP20K600E devices have 16 LABs, and the EP20K1000E and EP20K1500E devices have 24 LABs. Signals are routed between MegaLAB structures and I/O pins via the FastTrack Interconnect. In addition, edge LABs can be driven by I/O pins through the local interconnect. Figure 2 shows the MegaLAB structure.

Figure 2. MegaLAB Structure

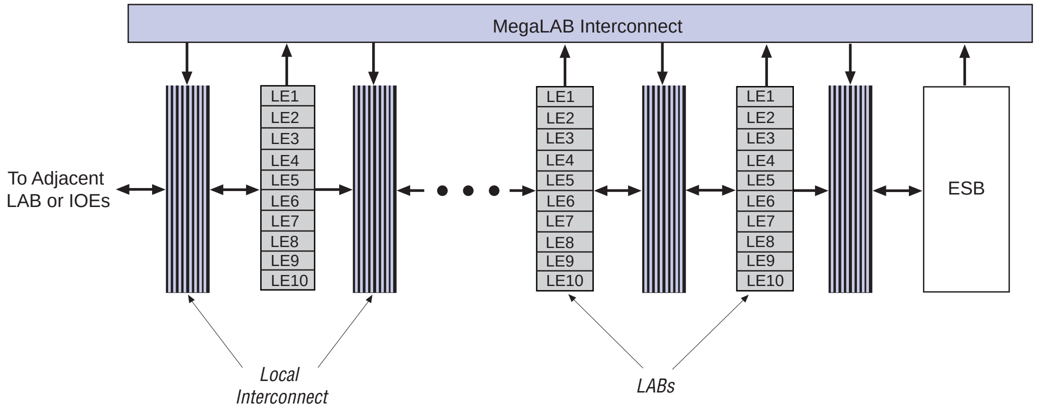
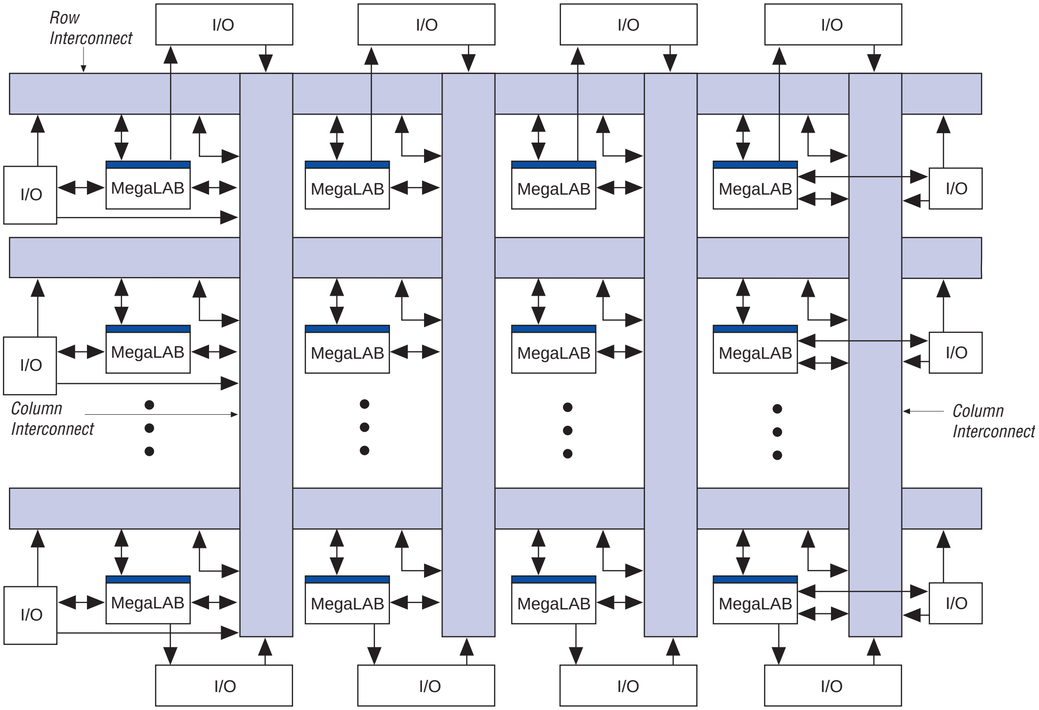


Figure 9. APEX 20K Interconnect Structure

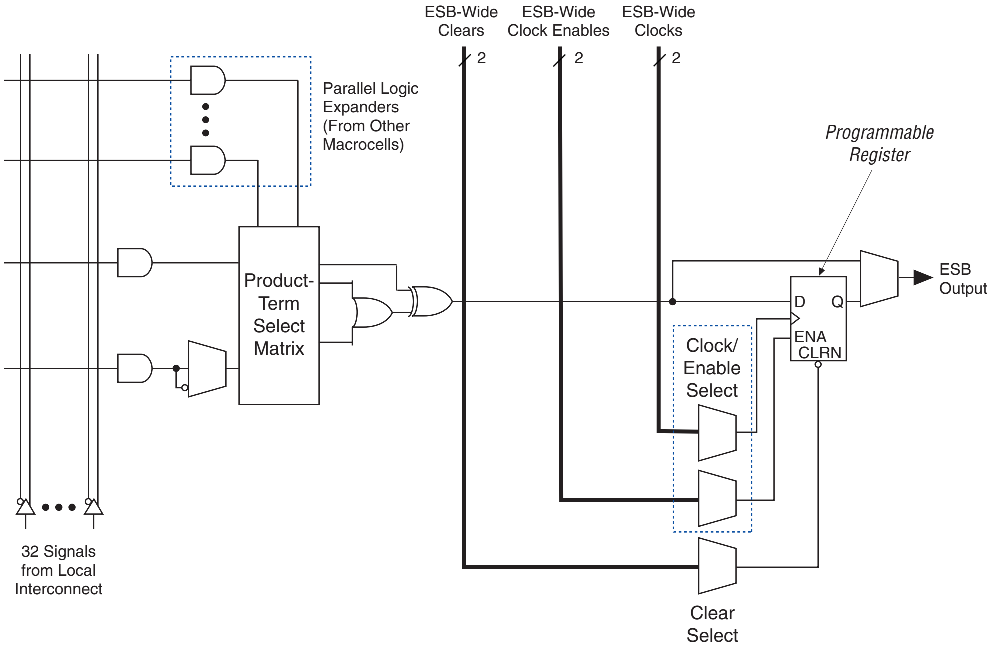


A row line can be driven directly by LEs, IOEs, or ESBs in that row. Further, a column line can drive a row line, allowing an LE, IOE, or ESB to drive elements in a different row via the column and row interconnect. The row interconnect drives the MegaLAB interconnect to drive LEs, IOEs, or ESBs in a particular MegaLAB structure.

A column line can be directly driven by LEs, IOEs, or ESBs in that column. A column line on a device's left or right edge can also be driven by row IOEs. The column line is used to route signals from one row to another. A column line can drive a row line; it can also drive the MegaLAB interconnect directly, allowing faster connections between rows.

Figure 10 shows how the FastTrack Interconnect uses the local interconnect to drive LEs within MegaLAB structures.

Figure 14. APEX 20K Macrocell



For registered functions, each macrocell register can be programmed individually to implement D, T, JK, or SR operation with programmable clock control. The register can be bypassed for combinatorial operation. During design entry, the designer specifies the desired register type; the Quartus II software then selects the most efficient register operation for each registered function to optimize resource utilization. The Quartus II software or other synthesis tools can also select the most efficient register operation automatically when synthesizing HDL designs.

Each programmable register can be clocked by one of two ESB-wide clocks. The ESB-wide clocks can be generated from device dedicated clock pins, global signals, or local interconnect. Each clock also has an associated clock enable, generated from the local interconnect. The clock and clock enable signals are related for a particular ESB; any macrocell using a clock also uses the associated clock enable.

If both the rising and falling edges of a clock are used in an ESB, both ESB-wide clock signals are used.

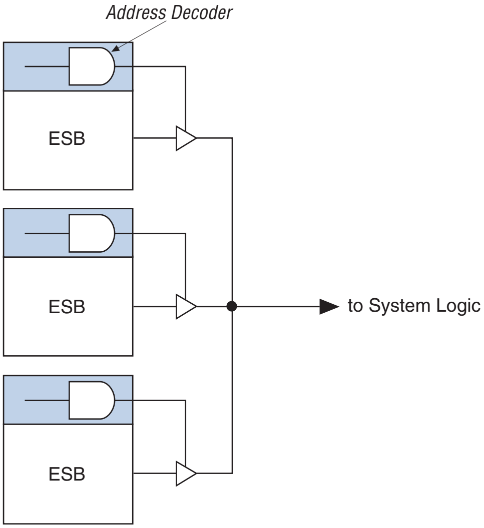
ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (`WE`) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the `WE` signal. In contrast, the ESB's synchronous RAM generates its own `WE` signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the MegaLAB or FastTrack Interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the MegaLAB and FastTrack Interconnect. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

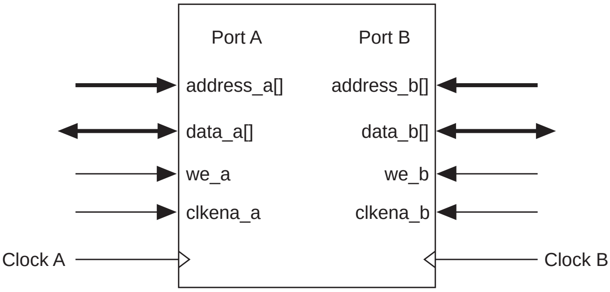
To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack Interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

Figure 18. Deep Memory Block Implemented with Multiple ESBs



The ESB implements two forms of dual-port memory: read/write clock mode and input/output clock mode. The ESB can also be used for bidirectional, dual-port memory applications in which two ports read or write simultaneously. To implement this type of dual-port memory, two or four ESBs are used to support two simultaneous reads or writes. This functionality is shown in Figure 19.

Figure 19. APEX 20K ESB Implementing Dual-Port RAM

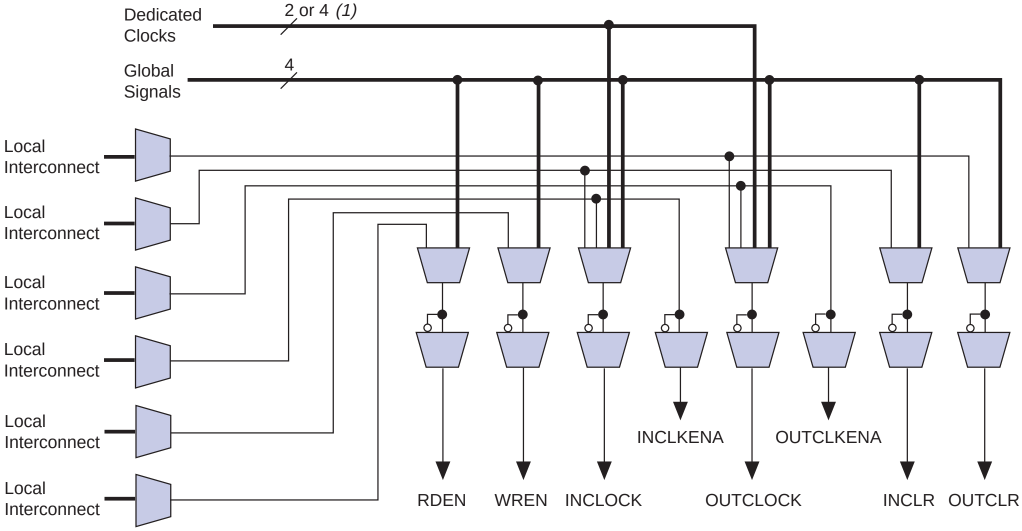


For more information on APEX 20KE devices and CAM, see *Application Note 119 (Implementing High-Speed Search Applications with APEX CAM).*

Driving Signals to the ESB

ESBs provide flexible options for driving control signals. Different clocks can be used for the ESB inputs and outputs. Registers can be inserted independently on the data input, data output, read address, write address, `WE`, and `RE` signals. The global signals and the local interconnect can drive the `WE` and `RE` signals. The global signals, dedicated clock pins, and local interconnect can drive the ESB clock signals. Because the LEs drive the local interconnect, the LEs can control the `WE` and `RE` signals and the ESB clock, clock enable, and asynchronous clear signals. Figure 24 shows the ESB control signal generation logic.

Figure 24. ESB Control Signal Generation

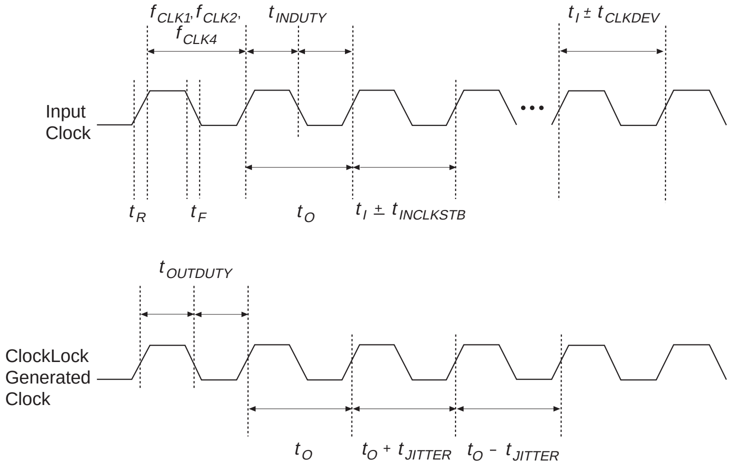


Note to Figure 24:

(1) APEX 20KE devices have four dedicated clocks.

An ESB is fed by the local interconnect, which is driven by adjacent LEs (for high-speed connection to the ESB) or the MegaLAB interconnect. The ESB can drive the local, MegaLAB, or FastTrack Interconnect routing structure to drive LEs and IOEs in the same MegaLAB structure or anywhere in the device.

Figure 30. Specifications for the Incoming & Generated Clocks *Note (1)*



Note to Figure 30:

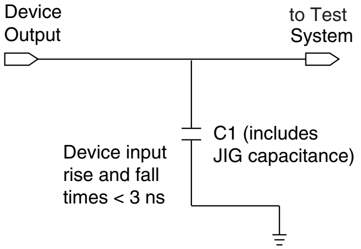
(1) The tI parameter refers to the nominal input clock period; the tO parameter refers to the nominal output clock period.

Table 15 summarizes the APEX 20K ClockLock and ClockBoost parameters for -1 speed-grade devices.

Table 15. APEX 20K ClockLock & ClockBoost Parameters for -1 Speed-Grade Devices (Part 1 of 2)

Symbol	Parameter	Min	Max	Unit
f_{OUT}	Output frequency	25	180	MHz
f_{CLK1} *(1)*	Input clock frequency (ClockBoost clock multiplication factor equals 1)	25	180 *(1)*	MHz
f_{CLK2}	Input clock frequency (ClockBoost clock multiplication factor equals 2)	16	90	MHz
f_{CLK4}	Input clock frequency (ClockBoost clock multiplication factor equals 4)	10	48	MHz
$t_{OUTDUTY}$	Duty cycle for ClockLock/ClockBoost-generated clock	40	60	%
f_{CLKDEV}	Input deviation from user specification in the Quartus II software (ClockBoost clock multiplication factor equals 1) *(2)*		25,000 *(3)*	PPM
t_R	Input rise time		5	ns
t_F	Input fall time		5	ns
t_{LOCK}	Time required for ClockLock/ClockBoost to acquire lock *(4)*		10	µs

Figure 32. APEX 20K AC Test Conditions *Note (1)*



Note to Figure 32:

(1) Power supply transients can affect AC measurements. Simultaneous transitions of multiple outputs should be avoided for accurate measurement. Threshold tests must not be performed under AC conditions. Large-amplitude, fast-ground-current transients normally occur as the device outputs discharge the load capacitances. When these transients flow through the parasitic inductance between the device ground pin and the test system ground, significant reductions in observable noise immunity can result.

Operating Conditions

Tables 23 through 26 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 2.5-V APEX 20K devices.

Table 23. APEX 20K 5.0-V Tolerant Device Absolute Maximum Ratings *Notes (1), (2)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage	With respect to ground *(3)*	–0.5	3.6	V
V_{CCIO}			–0.5	4.6	V
V_I	DC input voltage		–2.0	5.75	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	PQFP, RQFP, TQFP, and BGA packages, under bias		135	° C
		Ceramic PGA packages, under bias		150	° C

Table 24. APEX 20K 5.0-V Tolerant Device Recommended Operating Conditions *Note (2)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(4)*, *(5)*	2.375 (2.375)	2.625 (2.625)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	*(4)*, *(5)*	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	*(4)*, *(5)*	2.375 (2.375)	2.625 (2.625)	V
V_I	Input voltage	*(3)*, *(6)*	–0.5	5.75	V
V_O	Output voltage		0	V_{CCIO}	V
T_J	Junction temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Table 25. APEX 20K 5.0-V Tolerant Device DC Operating Conditions (Part 1 of 2) *Notes (2), (7), (8)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		1.7, 0.5 × V_{CCIO} *(9)*		5.75	V
V_{IL}	Low-level input voltage		–0.5		0.8, 0.3 × V_{CCIO} *(9)*	V
V_{OH}	3.3-V high-level TTL output voltage	I_{OH} = –8 mA DC, V_{CCIO} = 3.00 V *(10)*	2.4			V
	3.3-V high-level CMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(10)*	V_{CCIO} – 0.2			V
	3.3-V high-level PCI output voltage	I_{OH} = –0.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(10)*	0.9 × V_{CCIO}			V
	2.5-V high-level output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 2.30 V *(10)*	2.1			V
		I_{OH} = –1 mA DC, V_{CCIO} = 2.30 V *(10)*	2.0			V
		I_{OH} = –2 mA DC, V_{CCIO} = 2.30 V *(10)*	1.7			V

Table 26. APEX 20K 5.0-V Tolerant Device Capacitance *Notes (2), (14)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Notes to Tables 23 through 26:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) All APEX 20K devices are 5.0-V tolerant.
(3) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to 5.75 V for input currents less than 100 mA and periods shorter than 20 ns.
(4) Numbers in parentheses are for industrial-temperature-range devices.
(5) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
(6) All pins, including dedicated inputs, clock I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
(7) Typical values are for T_A= 25° C, V_{CCINT} = 2.5 V, and V_{CCIO} = 2.5 or 3.3 V.
(8) These values are specified in the APEX 20K device recommended operating conditions, shown in Table 26 on page 62.
(9) The APEX 20K input buffers are compatible with 2.5-V and 3.3-V (LVTTL and LVCMOS) signals. Additionally, the input buffers are 3.3-V PCI compliant when V_{CCIO} and V_{CCINT} meet the relationship shown in Figure 33 on page 68.
(10) The I_{OH} parameter refers to high-level TTL, PCI or CMOS output current.
(11) The I_{OL} parameter refers to low-level TTL, PCI, or CMOS output current. This parameter applies to open-drain pins as well as output pins.
(12) This value is specified for normal device operation. The value may vary during power-up.
(13) Pin pull-up resistance values will be lower if an external source drives the pin higher than V_{CCIO}.
(14) Capacitance is sample-tested only.

Tables 27 through 30 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 1.8-V APEX 20KE devices.

Table 27. APEX 20KE Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage	With respect to ground *(2)*	–0.5	2.5	V
V_{CCIO}			–0.5	4.6	V
V_I	DC input voltage		–0.5	4.6	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	PQFP, RQFP, TQFP, and BGA packages, under bias		135	° C
		Ceramic PGA packages, under bias		150	° C

For DC Operating Specifications on APEX 20KE I/O standards, please refer to *Application Note 117 (Using Selectable I/O Standards in Altera Devices).*

Table 30. APEX 20KE Device Capacitance Note (15)

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Notes to Tables 27 through 30:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to 5.75 V for input currents less than 100 mA and periods shorter than 20 ns.
(3) Numbers in parentheses are for industrial-temperature-range devices.
(4) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
(5) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to the voltage shown in the following table based on input duty cycle for input currents less than 100 mA. The overshoot is dependent upon duty cycle of the signal. The DC case is equivalent to 100% duty cycle.

Vin	Max. Duty Cycle
4.0V	100% (DC)
4.1	90%
4.2	50%
4.3	30%
4.4	17%
4.5	10%

(6) All pins, including dedicated inputs, clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
(7) Typical values are for T_A = 25° C, V_{CCINT} = 1.8 V, and V_{CCIO} = 1.8 V, 2.5 V or 3.3 V.
(8) These values are specified under the APEX 20KE device recommended operating conditions, shown in Table 24 on page 60.
(9) Refer to *Application Note 117 (Using Selectable I/O Standards in Altera Devices)* for the V_{IH}, V_{IL}, V_{OH}, V_{OL}, and I_I parameters when VCCIO = 1.8 V.
(10) The APEX 20KE input buffers are compatible with 1.8-V, 2.5-V and 3.3-V (LVTTL and LVCMOS) signals. Additionally, the input buffers are 3.3-V PCI compliant. Input buffers also meet specifications for GTL+, CTT, AGP, SSTL-2, SSTL-3, and HSTL.
(11) The I_{OH} parameter refers to high-level TTL, PCI, or CMOS output current.
(12) The I_{OL} parameter refers to low-level TTL, PCI, or CMOS output current. This parameter applies to open-drain pins as well as output pins.
(13) This value is specified for normal device operation. The value may vary during power-up.
(14) Pin pull-up resistance values will be lower if an external source drives the pin higher than V_{CCIO}.
(15) Capacitance is sample-tested only.

Figure 33 shows the relationship between V_{CCIO} and V_{CCINT} for 3.3-V PCI compliance on APEX 20K devices.

Figure 39. ESB Synchronous Timing Waveforms

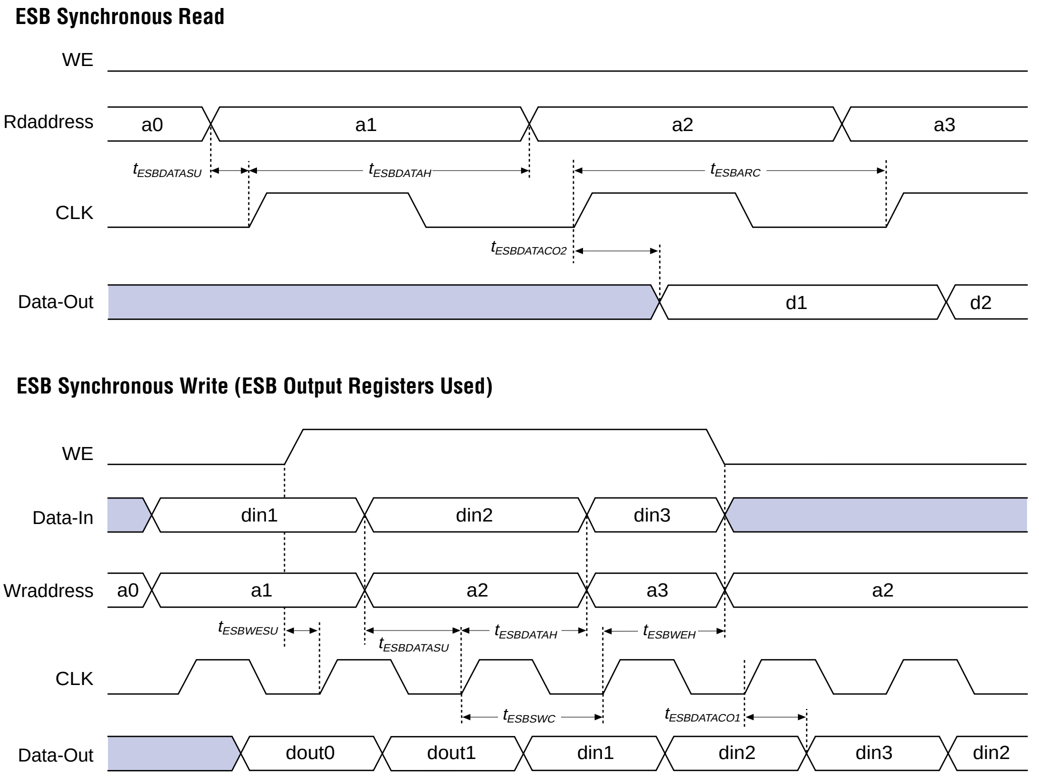


Figure 40 shows the timing model for bidirectional I/O pin timing.

Table 43. EP20K100 External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU} *(1)*	2.3		2.8		3.2		ns
t_{INH} *(1)*	0.0		0.0		0.0		ns
t_{OUTCO} *(1)*	2.0	4.5	2.0	4.9	2.0	6.6	ns
t_{INSU} *(2)*	1.1		1.2		–		ns
t_{INH} *(2)*	0.0		0.0		–		ns
t_{OUTCO} *(2)*	0.5	2.7	0.5	3.1	–	4.8	ns

Table 44. EP20K100 External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ *(1)*	2.3		2.8		3.2		ns
$t_{INHBIDIR}$ *(1)*	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$ *(1)*	2.0	4.5	2.0	4.9	2.0	6.6	ns
$t_{XZBIDIR}$ *(1)*		5.0		5.9		6.9	ns
$t_{ZXBIDIR}$ *(1)*		5.0		5.9		6.9	ns
$t_{INSUBIDIR}$ *(2)*	1.0		1.2		–		ns
$t_{INHBIDIR}$ *(2)*	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ *(2)*	0.5	2.7	0.5	3.1	–	–	ns
$t_{XZBIDIR}$ *(2)*		4.3		5.0		–	ns
$t_{ZXBIDIR}$ *(2)*		4.3		5.0		–	ns

Table 45. EP20K200 External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU} *(1)*	1.9		2.3		2.6		ns
t_{INH} *(1)*	0.0		0.0		0.0		ns
t_{OUTCO} *(1)*	2.0	4.6	2.0	5.6	2.0	6.8	ns
t_{INSU} *(2)*	1.1		1.2		–		ns
t_{INH} *(2)*	0.0		0.0		–		ns
t_{OUTCO} *(2)*	0.5	2.7	0.5	3.1	–	–	ns

Tables 67 through 72 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K160E APEX 20KE devices.

Table 67. EP20K160E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.22		0.24		0.26		ns
t_{H}	0.22		0.24		0.26		ns
t_{CO}		0.25		0.31		0.35	ns
t_{LUT}		0.69		0.88		1.12	ns

Table 72. EP20K160E External Bidirectional Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.86		3.24		3.54		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	5.07	2.00	5.59	2.00	6.13	ns
$t_{XZBIDIR}$		7.43		8.23		8.58	ns
$t_{ZXBIDIR}$		7.43		8.23		8.58	ns
$t_{INSUBIDIRPLL}$	4.93		5.48		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	3.00	0.50	3.35	-	-	ns
$t_{XZBIDIRPLL}$		5.36		5.99		-	ns
$t_{ZXBIDIRPLL}$		5.36		5.99		-	ns

Tables 73 through 78 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K200E APEX 20KE devices.

Table 73. EP20K200E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.23		0.24		0.26		ns
t_H	0.23		0.24		0.26		ns
t_{CO}		0.26		0.31		0.36	ns
t_{LUT}		0.70		0.90		1.14	ns

Table 99. EP20K1000E f_{MAX} Routing Delays

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.27		0.27		0.27	ns
t_{F5-20}		1.45		1.63		1.75	ns
t_{F20+}		4.15		4.33		4.97	ns

Table 100. EP20K1000E Minimum Pulse Width Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.25		1.43		1.67		ns
t_{CL}	1.25		1.43		1.67		ns
t_{CLRP}	0.20		0.20		0.20		ns
t_{PREP}	0.20		0.20		0.20		ns
t_{ESBCH}	1.25		1.43		1.67		ns
t_{ESBCL}	1.25		1.43		1.67		ns
t_{ESBWP}	1.28		1.51		1.65		ns
t_{ESBRP}	1.11		1.29		1.41		ns

Table 101. EP20K1000E External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.70		2.84		2.97		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	5.75	2.00	6.33	2.00	6.90	ns
$t_{INSUPLL}$	1.64		2.09		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.25	0.50	2.99	-	-	ns

Table 106. EP20K1500E Minimum Pulse Width Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.25		1.43		1.67		ns
t_{CL}	1.25		1.43		1.67		ns
t_{CLRP}	0.20		0.20		0.20		ns
t_{PREP}	0.20		0.20		0.20		ns
t_{ESBCH}	1.25		1.43		1.67		ns
t_{ESBCL}	1.25		1.43		1.67		ns
t_{ESBWP}	1.28		1.51		1.65		ns
t_{ESBRP}	1.11		1.29		1.41		ns

Table 107. EP20K1500E External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	3.09		3.30		3.58		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	6.18	2.00	6.81	2.00	7.36	ns
$t_{INSUPLL}$	1.94		2.08		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.67	0.50	2.99	-	-	ns

101 Innovation Drive
San Jose, CA 95134
(408) 544-7000
http://www.altera.com
Applications Hotline:
(800) 800-EPLD
Customer Marketing:
(408) 544-7104
Literature Services:
lit_req@altera.com

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